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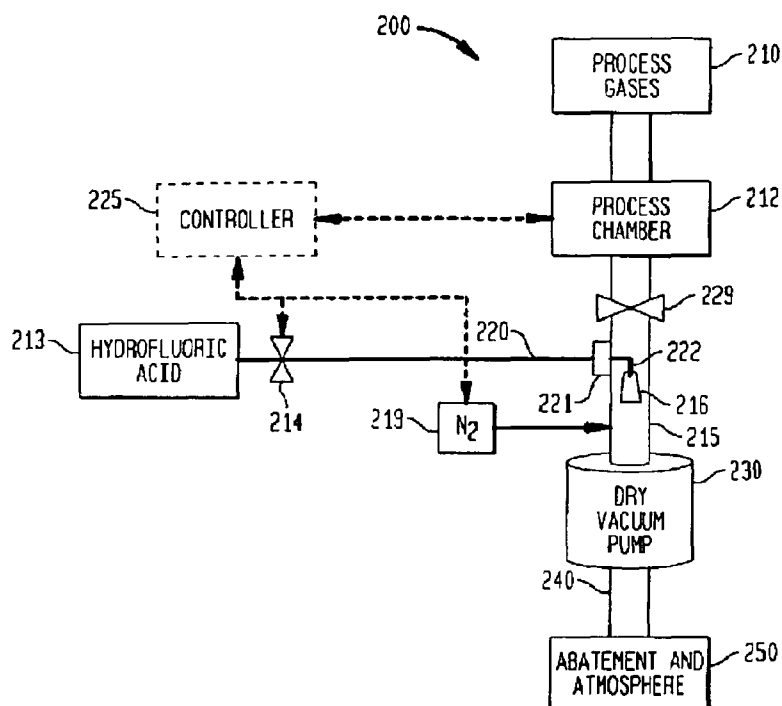
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(54) Title: IN-SITU REMOVAL OF SEMICONDUCTOR PROCESS RESIDUES FROM DRY PUMP SURFACES

FIG. 2



(57) Abstract: The present invention relates to vacuum processing systems in which process gases are introduced in a process chamber and are exhausted through a vacuum processing system exhaust path. Deposits made by the exhausted gases in one or more dry vacuum pumps are removed by introducing hydrofluoric acid upstream of the dry pump while the processing chamber is idle. The hydrofluoric acid is introduced upstream of the dry pump through a nozzle in the foreline or at the inlet to the dry pump.